查询IXFH30N50供应商

IXYS

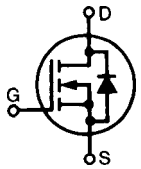
HiPerFET™ Power MOSFETs

N-Channel Enhancement Mode
High dv/dt, Low t_{rr}, HDMOS™ Family

IXFH/IXFT 30N50
IXFH/IXFT 32N50

V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	30 A	0.16 Ω
500 V	32 A	0.15 Ω

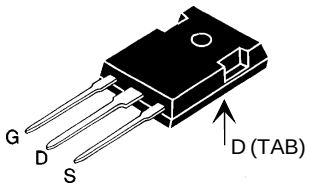
$t_{rr} \leq 250$ ns



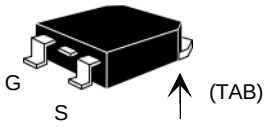
Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		500	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ		500	V
V_{GS}	Continuous		±20	V
V_{GSM}	Transient	±30	V	
I_{D25}	T_C = 25°C	30N50	30	A
		32N50	32	A
I_{DM}	T_C = 25°C	30N50	120	A
	pulse width limited by T_{JM}	32N50	128	A
I_{AR}	T_C = 25°C	30N50	30	A
		32N50	32	A
E_{AS}	T_C = 25°C		1.5	J
E_{AR}	I_D = 25°C		45	mJ
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \leq V_{DSS}$, $T_J \leq 150$°C, R_G = 2 Ω		5	V/ns
P_D	T_C = 25°C		360	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque		1.13/10	Nm/lb.in.
Weight			6	g

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 1 mA		500			V
	V_{DSS} temperature coefficient			0.102		%/K
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA		2		4	V
	$V_{GS(th)}$ temperature coefficient			-0.206		%/K
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0		±100			nA
I_{DSS}	V_{DS} = 0.8 • V_{DSS}	T_J = 25°C	200			µA
	V_{GS} = 0 V	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15A	32N50			0.15	Ω
		30N50			0.16	Ω
	Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %					

TO-247 AD (IXFH)



TO-268 (D3) Case Style



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic Diode

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

IXYS reserves the right to change limits, test conditions, and dimensions.

97518H (6/99)

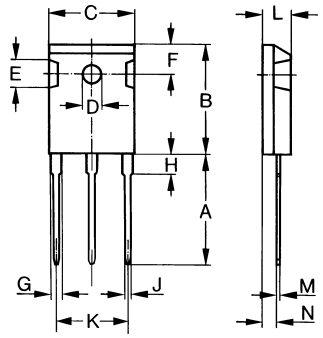
© 2000 IXYS All rights reserved

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 I_{D25}, pulse test	18	28		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	5200		5700	pF
C_{oss}		640		750	pF
C_{rss}		240		310	pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25} R_G = 2 Ω (External)		35	45	ns
t_r			42	50	ns
$t_{d(off)}$			110	140	ns
t_f			26	35	ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		227	300	nC
Q_{gs}			29	40	nC
Q_{gd}			110	145	nC
R_{thJC}				0.35	K/W
R_{thCK}	(TO-247 Case Style)		0.25		K/W

Source-Drain Diode

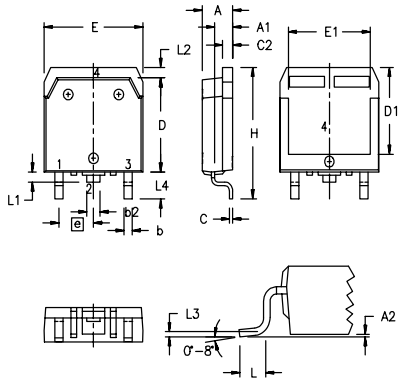
Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
I_S	V_{GS} = 0 V	30N50			30	A
		32N50			32	A
I_{SM}	Repetitive; pulse width limited by T_{JM}	30N50			120	A
		32N50			128	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %				1.5	V
t_{rr}	I_F = I_S -di/dt = 100 A/µs, V_R = 100 V	T_J = 25°C			250	ns
		T_J = 125°C			400	ns
Q_{RM}		T_J = 25°C		0.85		µC
I_{RM}		T_J = 25°C		8		A

TO-247 AD (IXFH) Outline



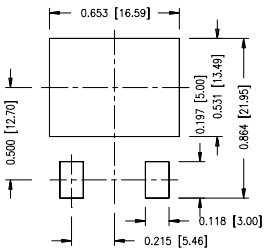
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-268AA (D^3 PAK)



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.9	5.1	.193	.201
A_1	2.7	2.9	.106	.114
A_2	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b_2	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E_1	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

Min. Recommended Footprint



© 2000 IXYS All rights reserved

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:
4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Figure 1. Output Characteristics at 25°C

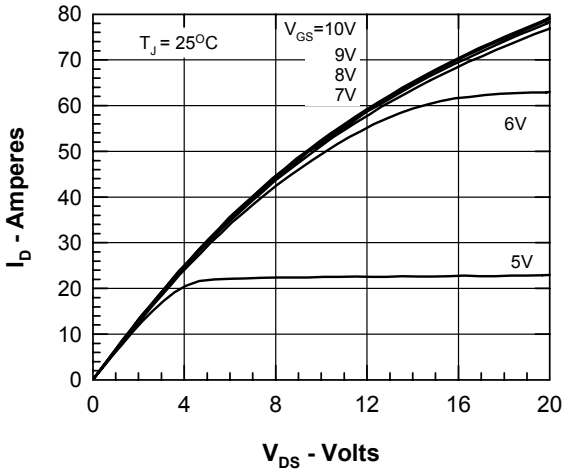


Figure 2. Output Characteristics at 125°C

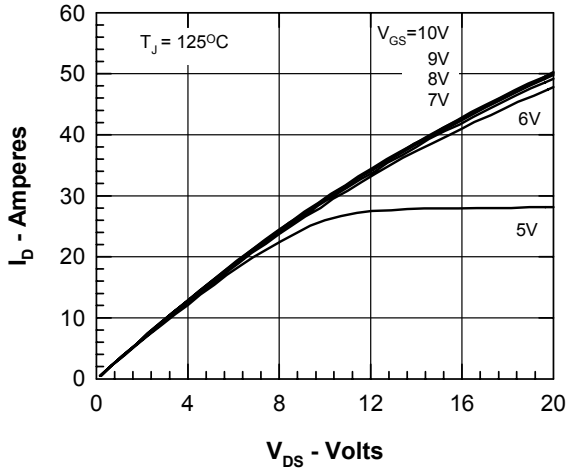


Figure 3. $R_{DS(on)}$ normalized to 15A/25°C vs. I_D

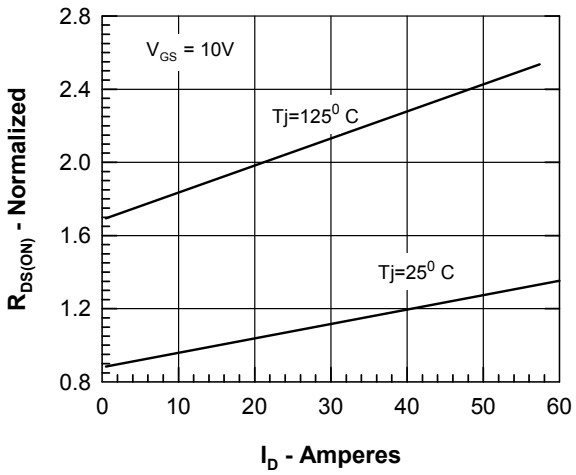


Figure 4. $R_{DS(on)}$ normalized to 15A/25°C vs. T_J

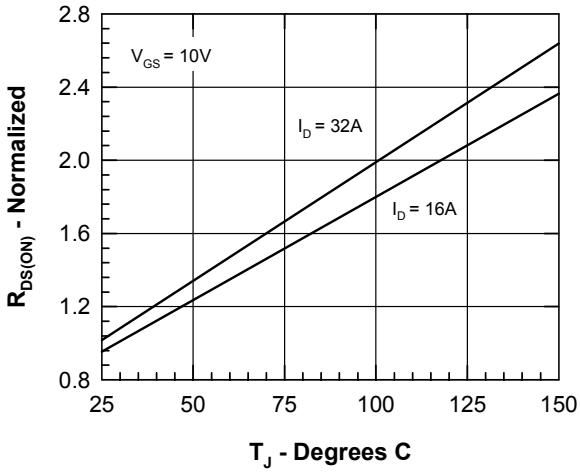


Figure 5. Drain Current vs. Case Temperature

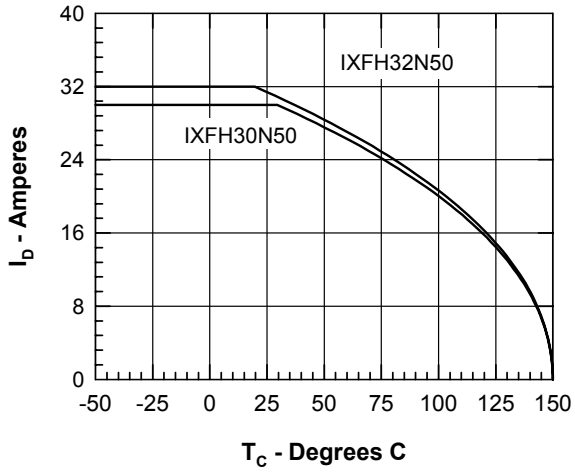
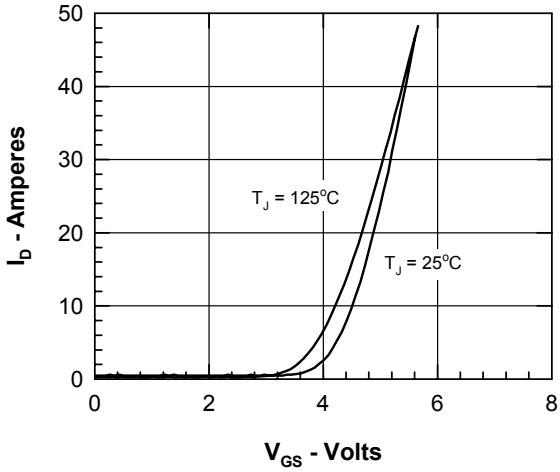


Figure 6. Admittance Curves



© 2000 IXYS All rights reserved

Figure 7. Gate Charge

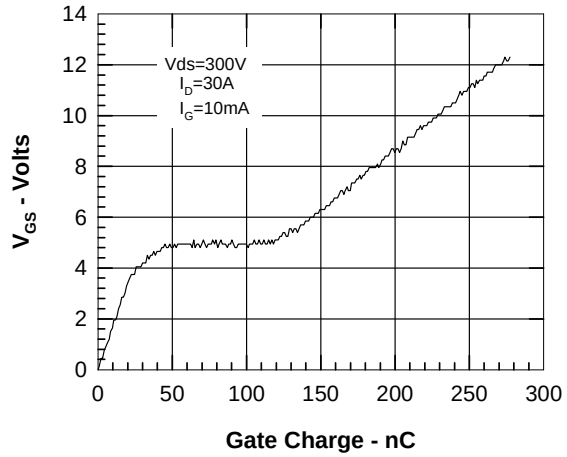


Figure 8. Capacitance Curves

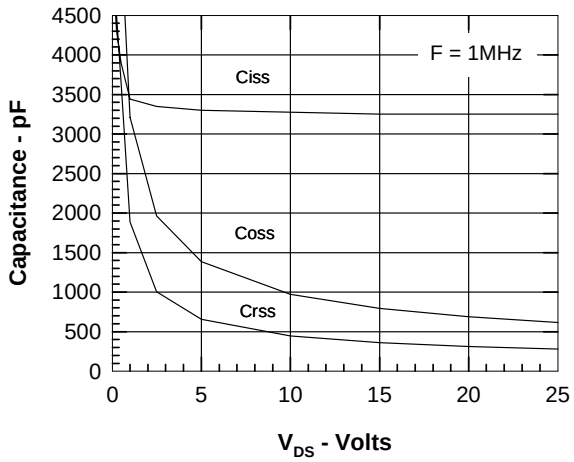


Figure 9. Forward Voltage Drop of the Intrinsic Diode

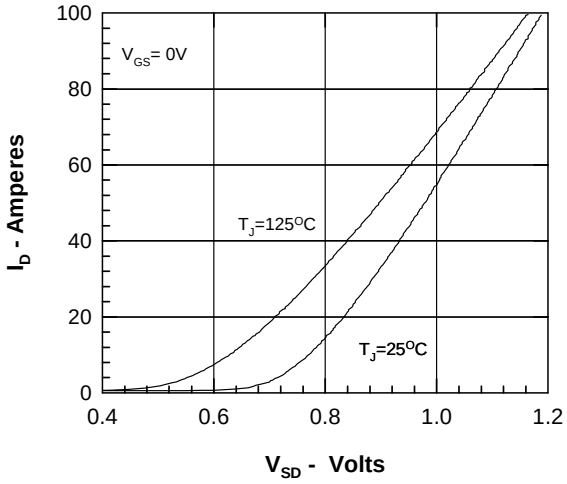
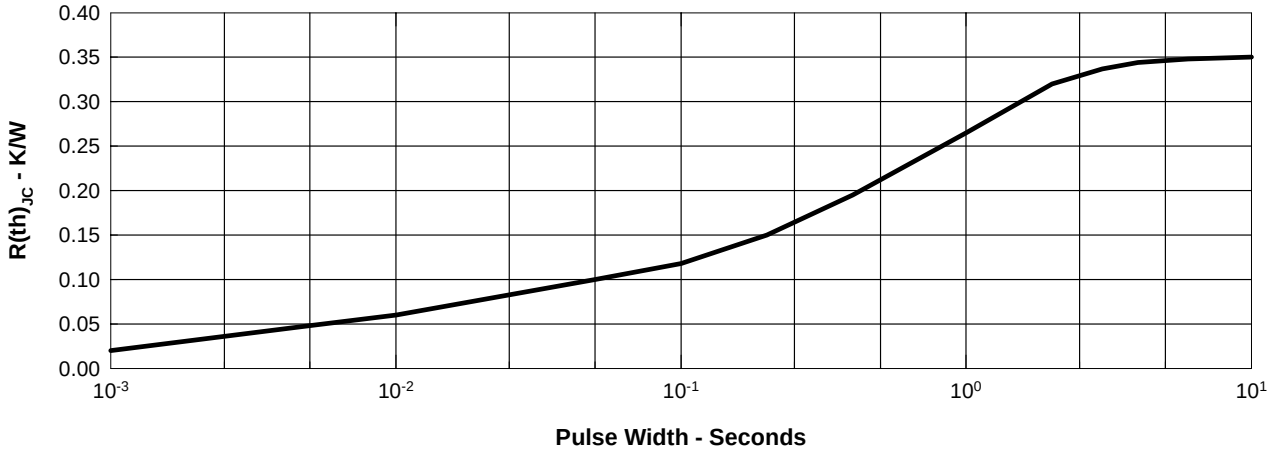


Figure 10. Transient Thermal Resistance



© 2000 IXYS All rights reserved